

Abstract of the Disclosure

A TFT fabricated from a single crystal grain, and fabrication method has been provided. A large crystal grain is made by precise control of annealment, transition metal concentration, the density of
5 transition metal nucleation sites, and the distance between nucleation sites. In one aspect of the invention, a diffusion layer permits the continual delivery of transition metal at a rate that both supports the lateral growth of di-silicide, and large distances between nucleation sites.

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